

N- and P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
	V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)	Q _g (Typ)
N-Channel	30	0.065 at V _{GS} = 10 V	4 ^a	2 nC
		0.100 at V _{GS} = 4.5 V	4 ^a	
P-Channel	- 30	0.140 at V _{GS} = - 10 V	- 3.7	2.2 nC
		0.235 at V _{GS} = - 4.5 V	- 2.8	

FEATURES

- TrenchFET[®] Power MOSFETs

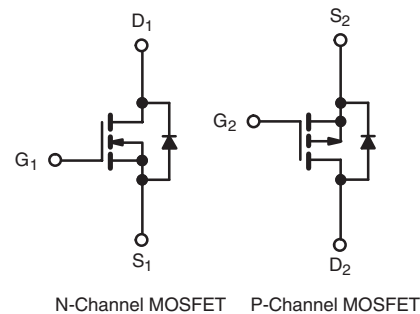
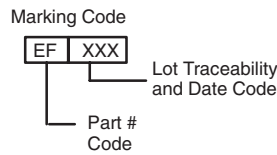
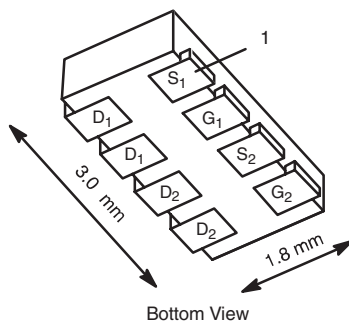
APPLICATIONS

- DC-DC for Portable Applications
- Load Switch



RoHS
COMPLIANT

1206-8 ChipFET[®] Dual



Ordering Information: Si5504BDC-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage	V _{DS}	30	- 30	V	
Gate-Source Voltage	V _{GS}	± 20			
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	4 ^a	- 3.7	A
		T _C = 85 °C	3.8	- 2.7	
		T _A = 25 °C	3.7 ^{b, c}	- 2.5 ^{b, c}	
		T _A = 85 °C	2.6 ^{b, c}	- 1.8 ^{b, c}	
Pulsed Drain Current	I _{DM}	10	- 10		
Source Drain Current Diode Current	I _S	T _C = 25 °C	2.5	- 2.5	
		T _A = 25 °C	1.3 ^{b, c}	- 1.3 ^{b, c}	
Maximum Power Dissipation	P _D	T _C = 25 °C	3.12	3.1	W
		T _C = 85 °C	2	2	
		T _A = 25 °C	1.5 ^{b, c}	1.5 ^{b, c}	
		T _A = 85 °C	0.8 ^{b, c}	0.8 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) ^{d, e}		260			

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	N-Channel		P-Channel		Unit
			Typ	Max	Typ	Max	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 sec	R _{thJA}	70	85	70	85	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	33	40	33	40	

Notes:

a. Package limited.

b. Surface Mounted on 1" x 1" FR4 Board.

c. t = 5 sec.

d. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under Steady State conditions is 120 °C/W.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	N-Ch	30		V
		$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-30		
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	N-Ch		27	mV/ $^\circ\text{C}$
		$I_D = -250\text{ }\mu\text{A}$	P-Ch		-30	
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$	N-Ch		-5	
		$I_D = -250\text{ }\mu\text{A}$	P-Ch		3.5	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	1.5		3
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-1.5		-3
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	N-Ch			100
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			-1
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$	N-Ch			5
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$	P-Ch			-5
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	N-Ch	10		A
		$V_{DS} \leq -5\text{ V}, V_{GS} = -10\text{ V}$	P-Ch	-10		
Drain-Source On-State Resistance ^b	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.1\text{ A}$	N-Ch		0.053	0.065
		$V_{GS} = -10\text{ V}, I_D = -2.1\text{ A}$	P-Ch		0.112	0.140
		$V_{GS} = 4.5\text{ V}, I_D = 1\text{ A}$	N-Ch		0.081	0.100
		$V_{GS} = -4.5\text{ V}, I_D = -0.43\text{ A}$	P-Ch		0.188	0.235
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 3.1\text{ A}$	N-Ch		5	S
		$V_{DS} = -15\text{ V}, I_D = -2.1\text{ A}$	P-Ch		3.5	
Dynamic^a						
Input Capacitance	C_{iss}	N-Channel $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		220	pF
Output Capacitance	C_{oss}		P-Ch		170	
Reverse Transfer Capacitance	C_{rss}	P-Channel $V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		50	
			P-Ch		50	
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 3.6\text{ A}$	N-Ch		4.5	7
		$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -2.5\text{ A}$	P-Ch		4.5	7
	Q_{gs}	N-Channel $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 3.6\text{ A}$	N-Ch		2	3
			P-Ch		2.2	3.5
Gate-Source Charge	Q_{gs}	P-Channel $V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$	N-Ch		0.7	
			P-Ch		0.7	
Gate-Drain Charge	Q_{gd}		N-Ch		0.7	
			P-Ch		1	
Gate Resistance	R_g	$f = 1\text{ MHz}$	N-Ch		3	Ω
			P-Ch		13	

Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.



SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Dynamic^a							
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 15\text{ V}, R_L = 5.8\ \Omega$ $I_D \cong 2.6\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\ \Omega$ P-Channel $V_{DD} = -15\text{ V}, R_L = 7.5\ \Omega$ $I_D \cong -2\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\ \Omega$	N-Ch		15	25	ns
			P-Ch		30	45	
Rise Time	t_r		N-Ch		80	120	
			P-Ch		60	90	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		12	20	
			P-Ch		10	15	
Fall Time	t_f		N-Ch		25	40	
			P-Ch		10	15	
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 15\text{ V}, R_L = 5.8\ \Omega$ $I_D \cong 2.6\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\ \Omega$ P-Channel $V_{DD} = -15\text{ V}, R_L = 7.5\ \Omega$ $I_D \cong -2\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\ \Omega$	N-Ch		4	8	
			P-Ch		4	8	
Rise Time	t_r		N-Ch		12	20	
			P-Ch		10	15	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		10	15	
			P-Ch		10	15	
Fall Time	t_f		N-Ch		5	10	
			P-Ch		5	10	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$	N-Ch			2.5	A
			P-Ch			-2.5	
Pulse Diode Forward Current ^a	I_{SM}		N-Ch			10	
			P-Ch			-10	
Body Diode Voltage	V_{SD}	$I_S = 2.6\text{ A}, V_{GS} = 0\text{ V}$ $I_S = -2\text{ A}, V_{GS} = 0\text{ V}$	N-Ch		0.8	1.2	V
			P-Ch		-0.8	-1.2	
Body Diode Reverse Recovery Time	t_{rr}	N-Channel $I_F = 2.6\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$ P-Channel $I_F = -2\text{ A}, di/dt = -100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$	N-Ch		30	50	ns
P-Ch			20	40			
Body Diode Reverse Recovery Charge	Q_{rr}		N-Ch		20	40	nC
			P-Ch		10	20	
Reverse Recovery Fall Time	t_a		N-Ch		23		ns
			P-Ch		13		
Reverse Recovery Rise Time	t_b		N-Ch		7		
			P-Ch		7		

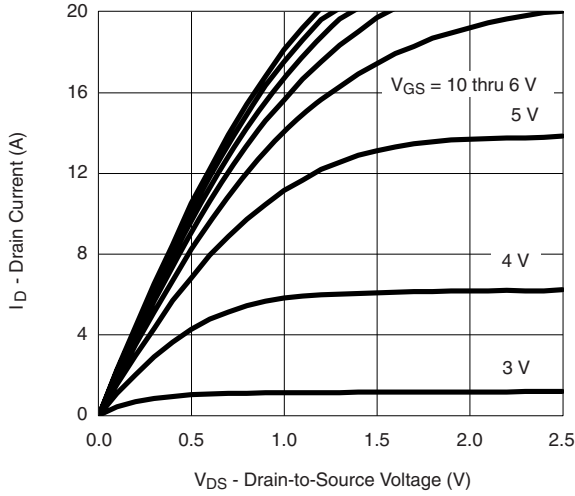
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

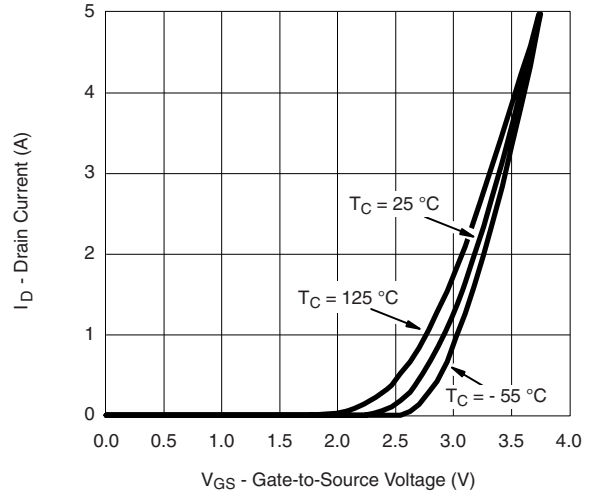
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



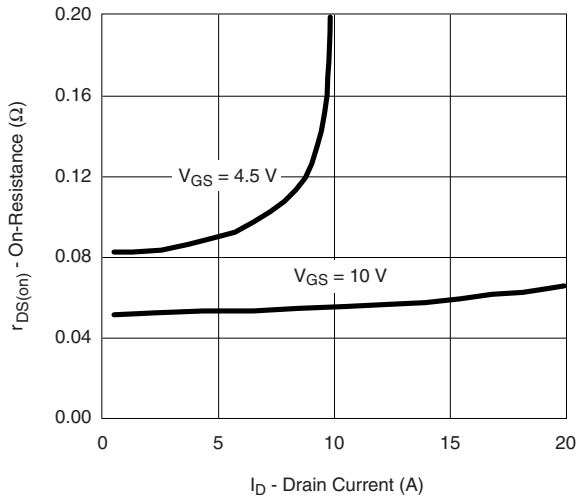
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



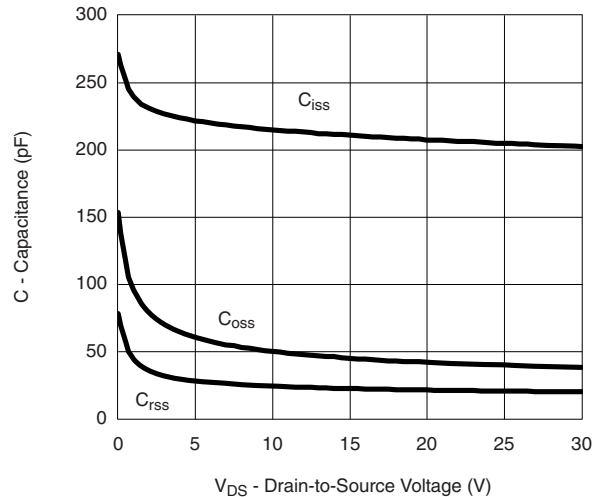
Output Characteristics



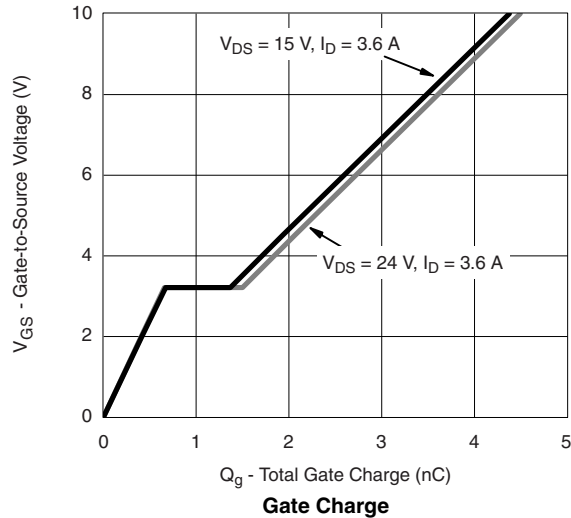
Transfer Characteristics



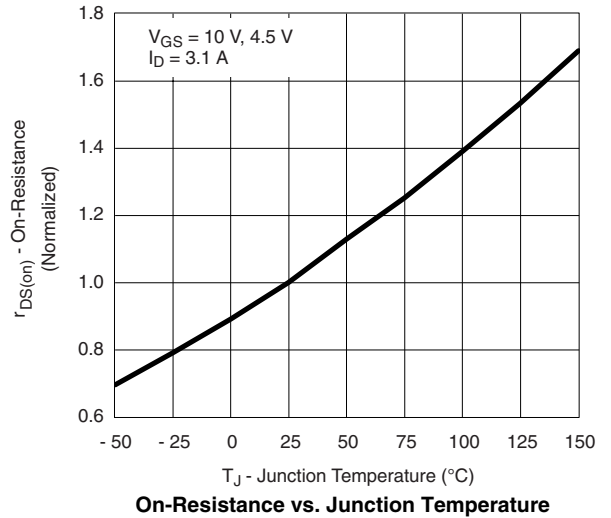
On-Resistance vs. Drain Current



Capacitance



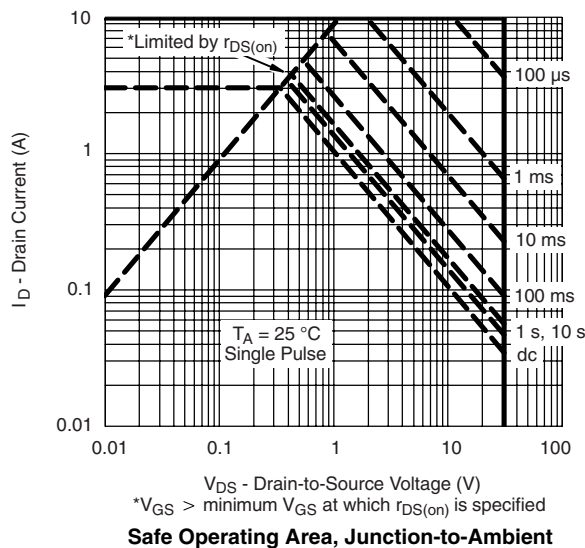
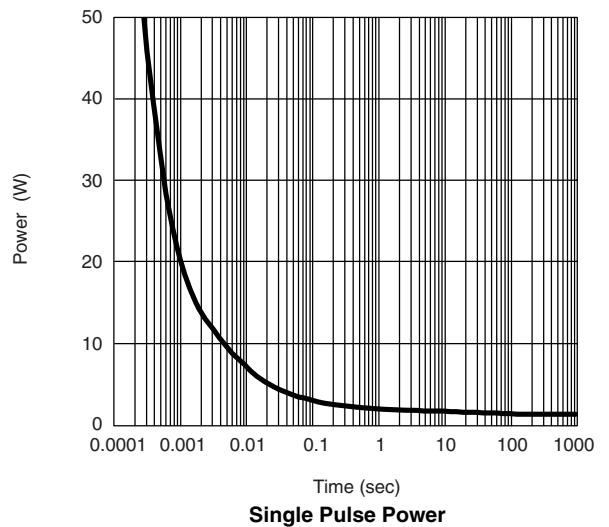
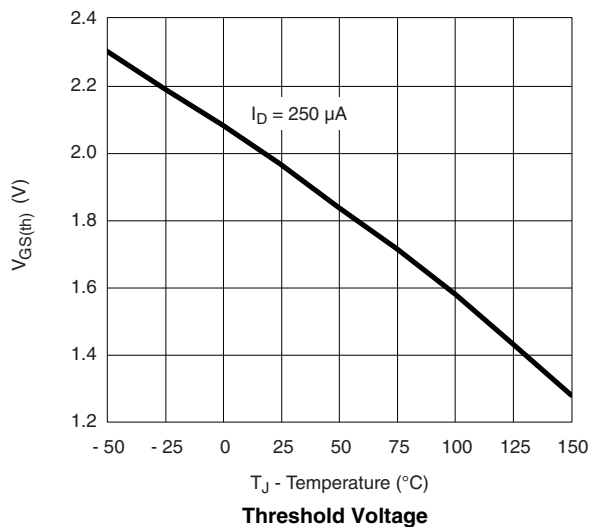
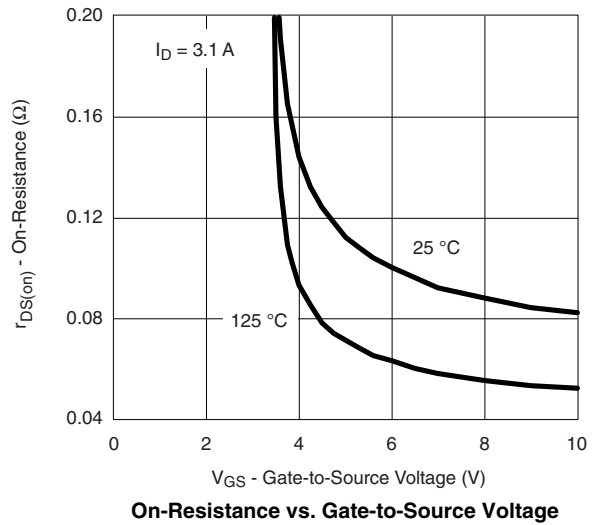
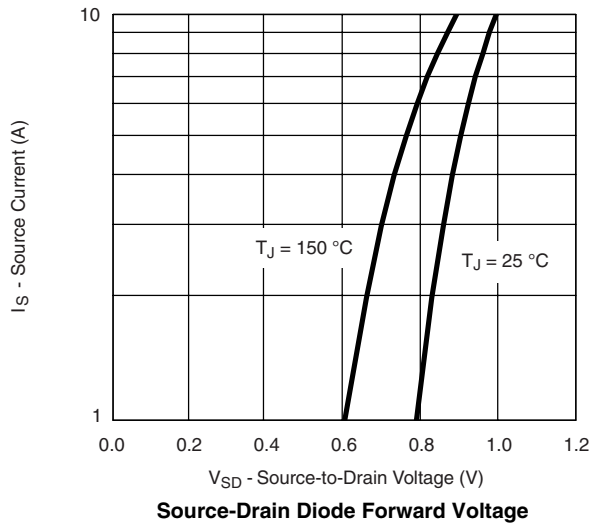
Gate Charge



On-Resistance vs. Junction Temperature

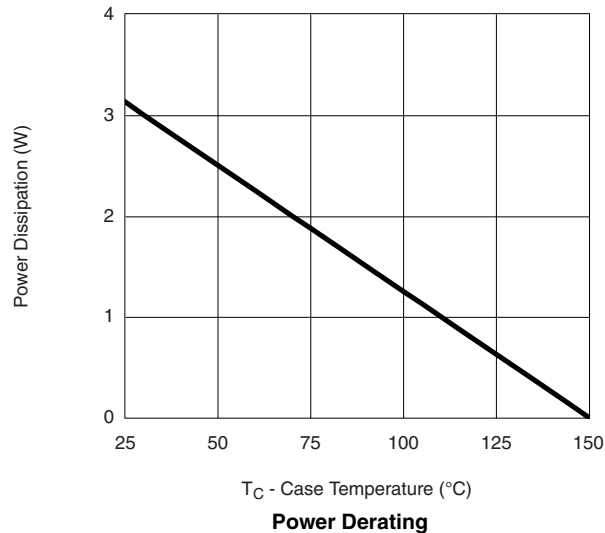
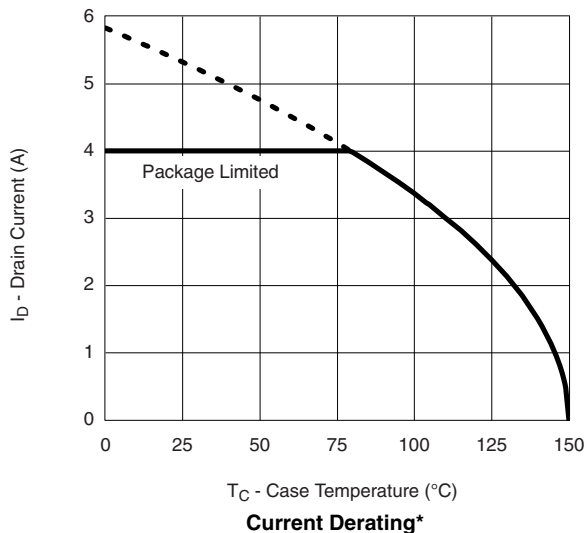


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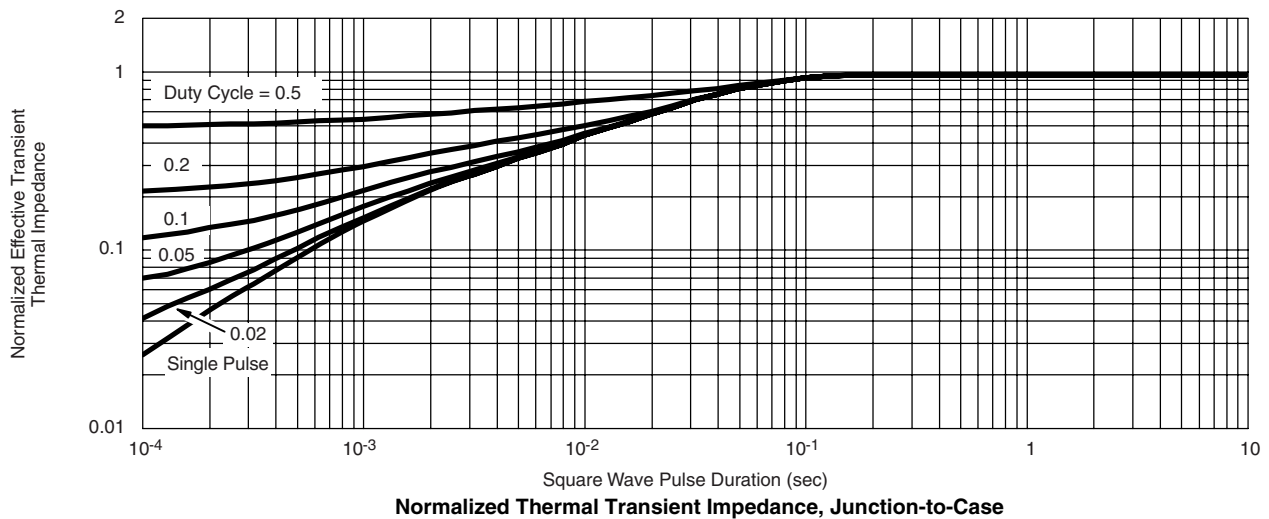
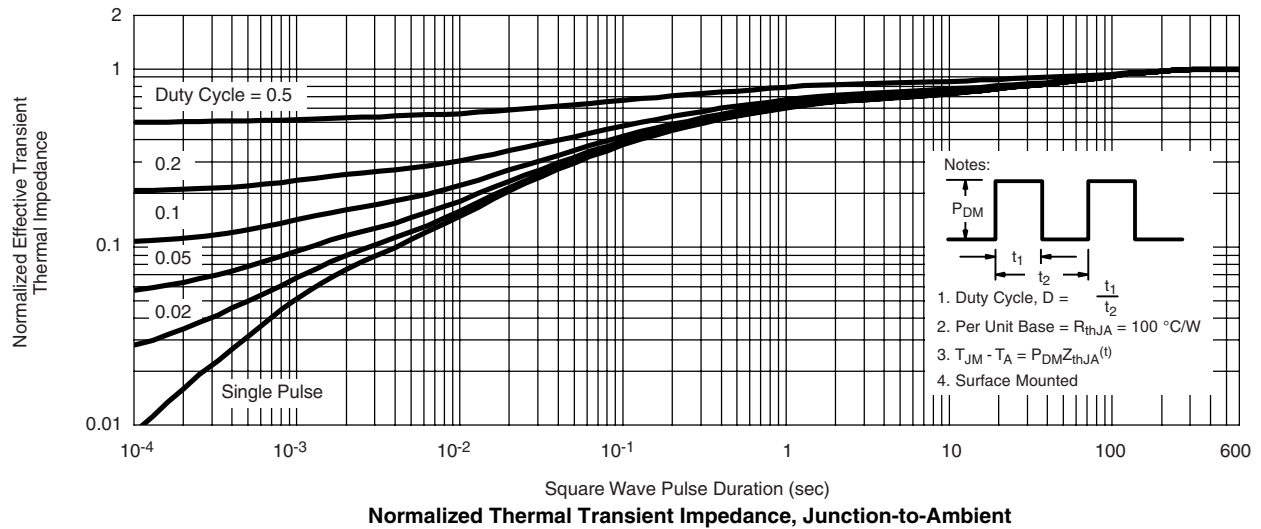
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



*The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

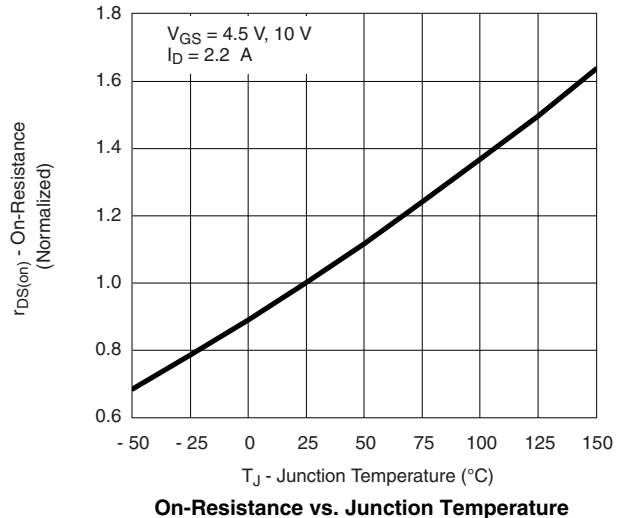
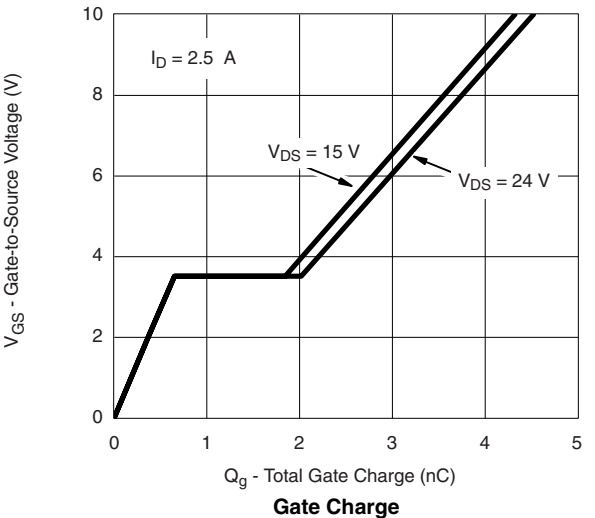
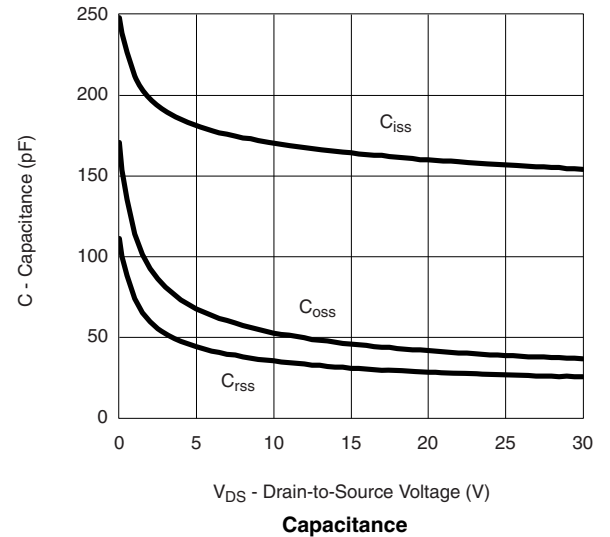
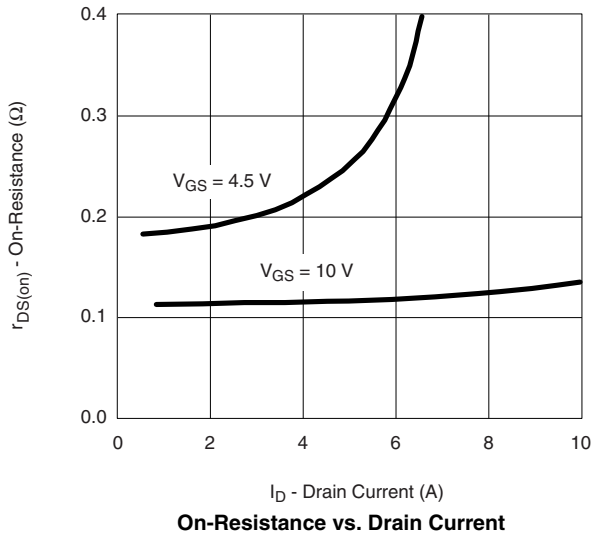
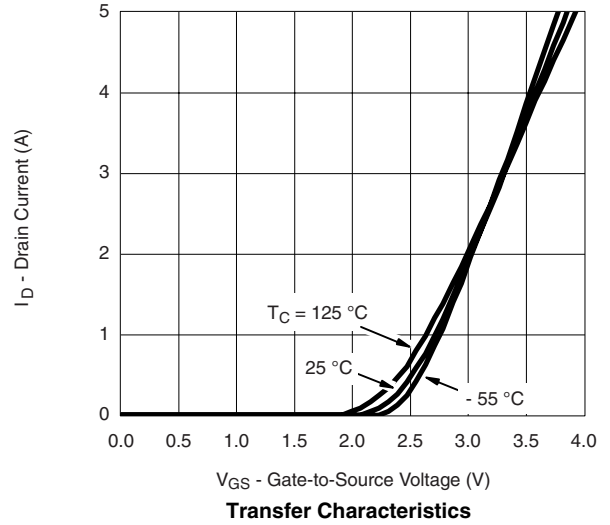
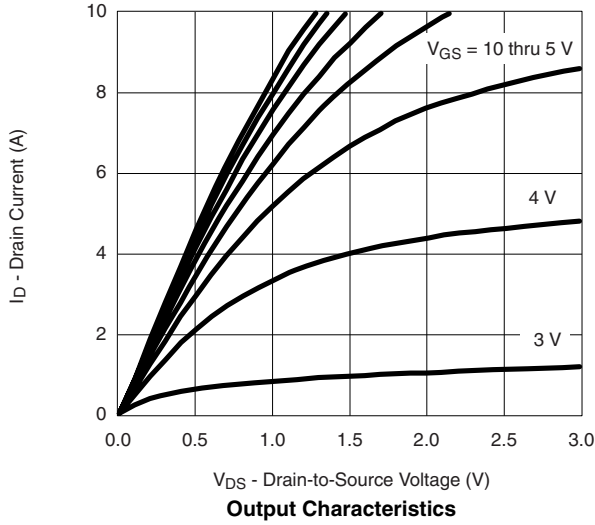


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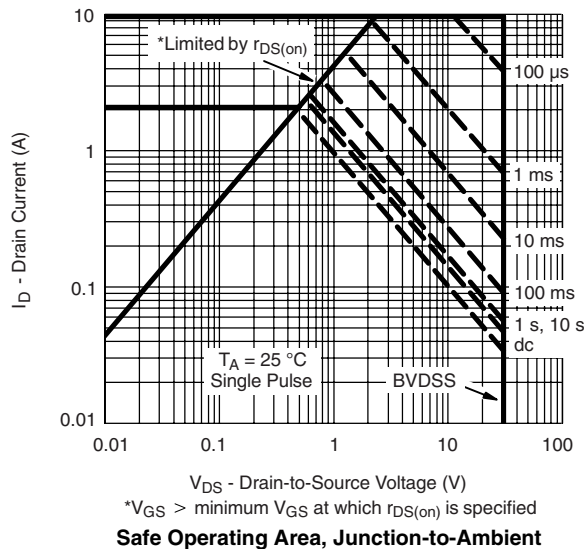
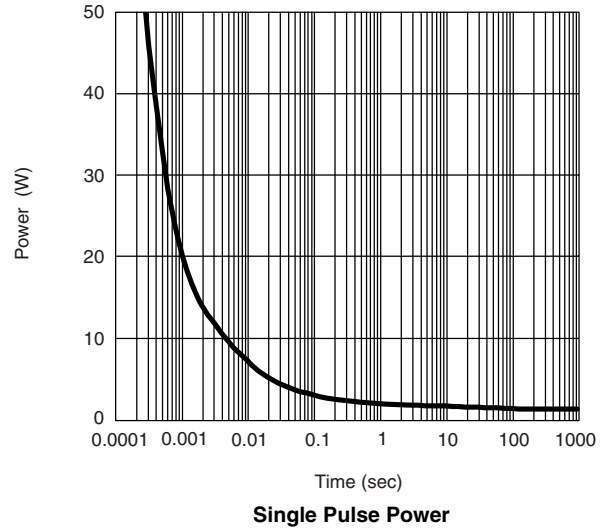
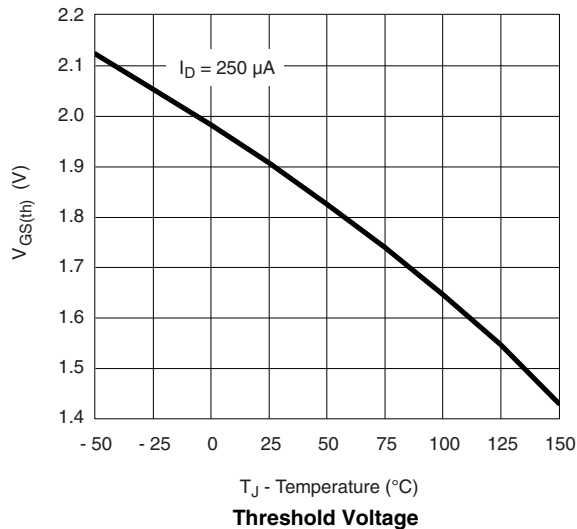
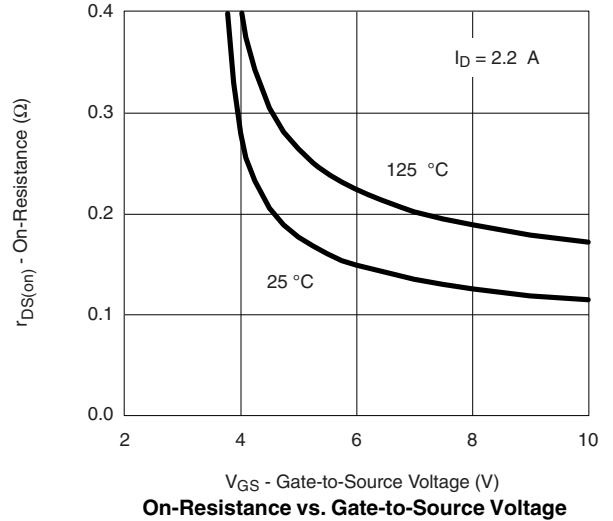
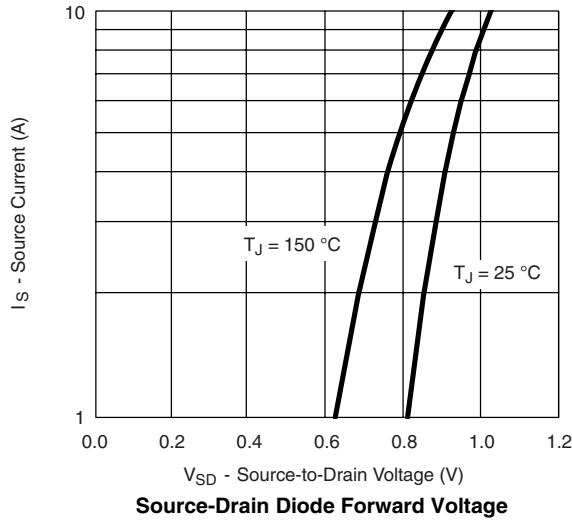


P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



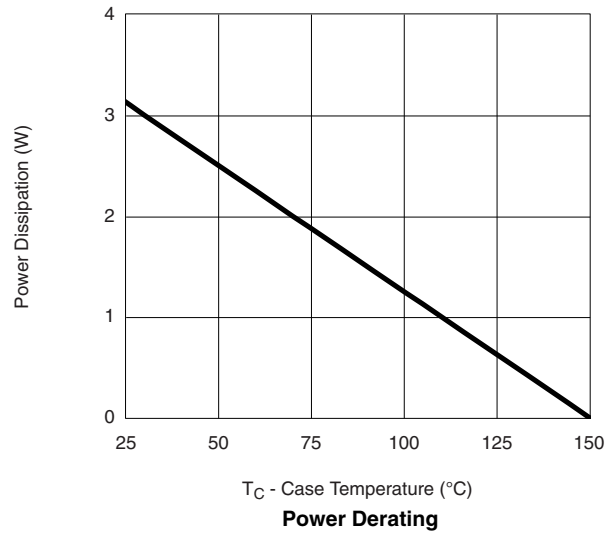
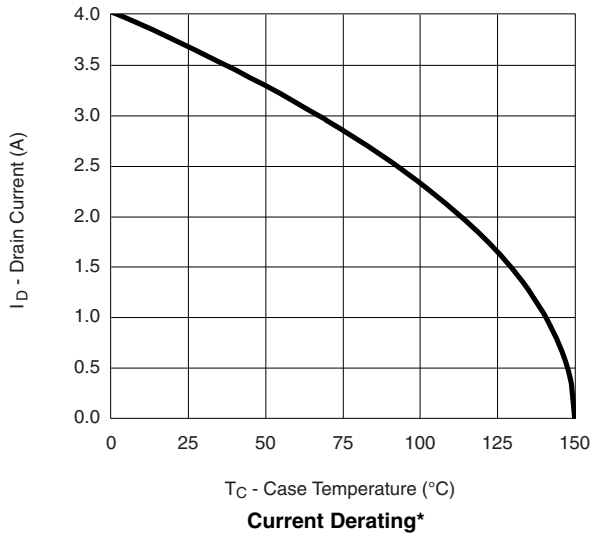


P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





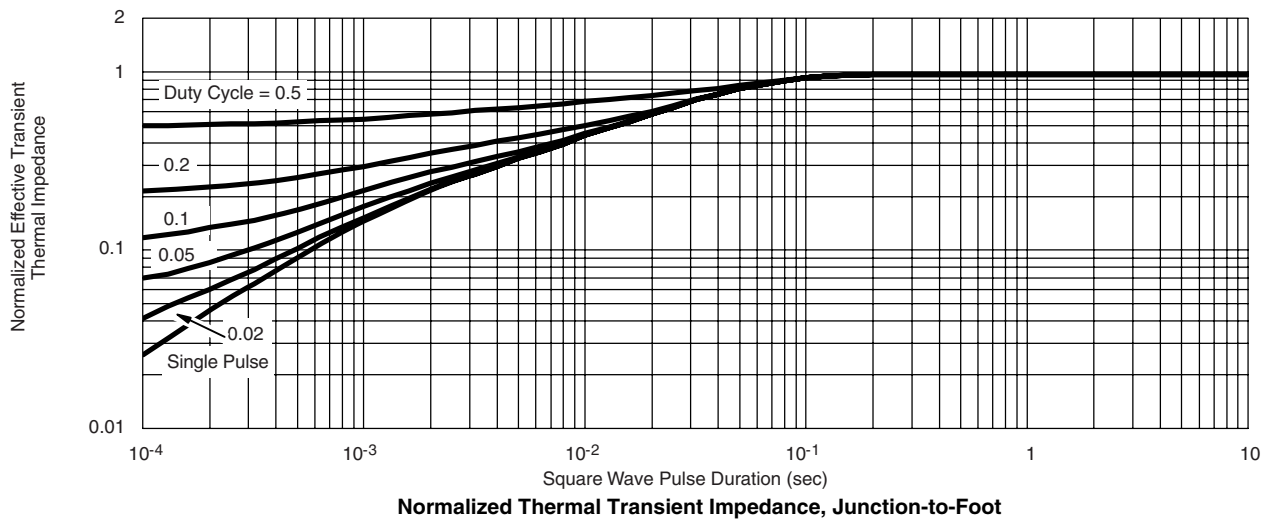
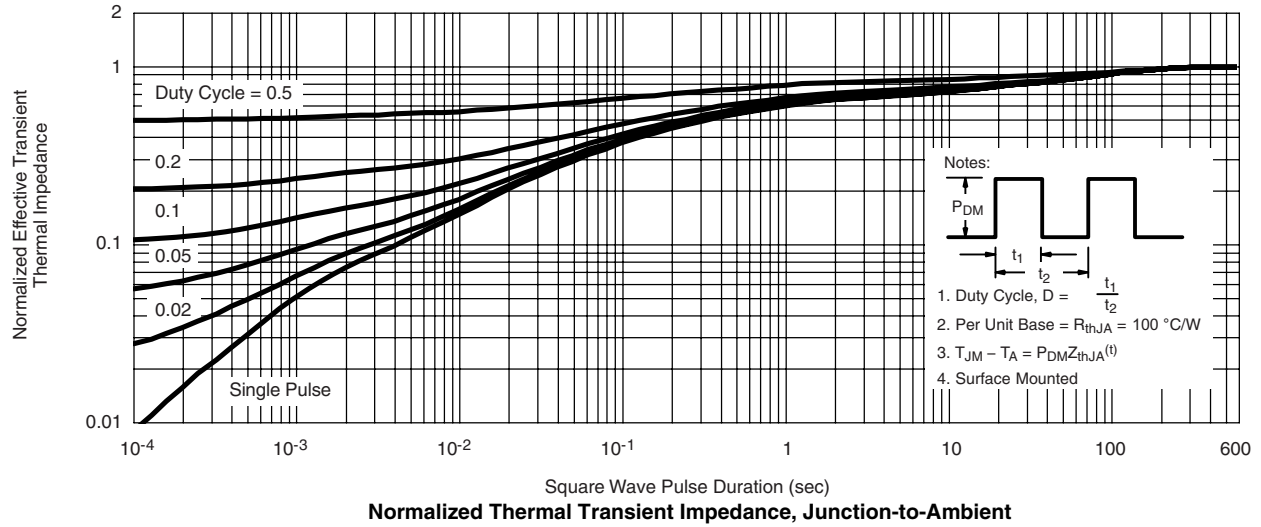
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P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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